

UTC D65H2 PNP EXPITAXIAL SILICON TRANSISTOR

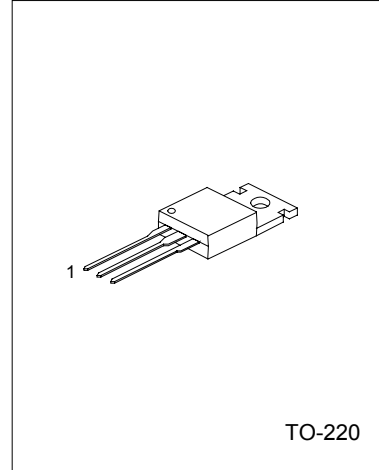
PNP EXPITAXIAL SILICON TRANSISTOR

DESCRIPTION

The UTC D65H2 is a general purpose power application and switching.

FEATURE

- *Low Collector-Emitter Saturation Voltage
 $V_{CE(sat)} = -1V(\text{MAX}) @ -15A$
- *Fast Switching Speeds



1:BASE 2:COLLECTOR 3:EMITTER

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ\text{C}$)

PARAMETER	SYMBOL	VALUE	UNIT
Collector to Emitter Voltage	V_{CEO}	-30	V
Emitter To Base Voltage	V_{EBO}	-5	V
Collector Current(DC)	I_C	-15	A
Collector Current(Pulse)	I_C	-25	A
Collector Dissipation($T_c = 25^\circ\text{C}$)	P_C	50	W
Collector Dissipation($T_a = 25^\circ\text{C}$)	P_C	1.67	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 ~ +150	$^\circ\text{C}$

* $P_W \leq 10\text{mS}$, Duty Cycle $\leq 50\%$

ELECTRICAL CHARACTERISTICS($T_a = 25^\circ\text{C}$)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector Cutoff Current	I_{CES}	$V_{CE} = \text{Rated} ; V_{CE0}, V_{EB} = 0$			-10	μA
Emitter Cutoff current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-10	μA
Collector Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C = -10A, I_B = -0.1A$			0.6	V
Base Emitter Saturation Voltage	$V_{BE(SAT)}$	$I_C = -10A, I_B = -1A$			-1.5	V
DC Current Gain	h_{FE1}	$I_C = -10A, V_{CE} = -1V$	100			
Current Gain Bandwidth Product	F_T	$V_{CE} = -10V, I_C = -0.5A$		40		MHZ
Output Capacitance	C_{CB}	$V_{CB} = -10V, f = 1\text{MHZ}$		350		PF
Turn On Time	t_{on}	$I_C = -5A, I_B = -0.5A$		150		nS
Storage Time	t_{stg}	$I_B = -0.5A$		600		nS
Fall Time	t_f			120		nS